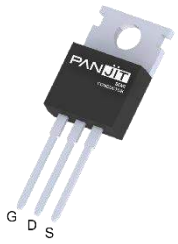
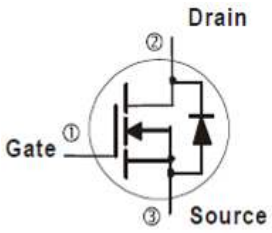
600V N-Channel Super Junction MOSFET

Voltage	**600 V**	**Rdson**	**120 mΩ**
Current	**30 A**	**Qg**	**51 nC**

TO-220AB-L





Feature:

- $R_{DS(ON)\ Max}$, V_{GS}@10V: 120mΩ
- Easy to use/ drive
- High Speed Switching and Low $R_{DS(ON)}$
- 100% Avalanche Tested
- 100% Rg Tested
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: TO-220AB-L package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0739 ounces, 2.0948 grams

Application

- PFC, TV Power, PC Power, PD Charger, Adapter, UPS

Absolute Maximum Ratings (T_A = 25 °C unless otherwise specified)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage @ T_{jmax}		V_{DS}	650	V
Drain-Source Voltage		V_{DS}	600	
Gate-Source Voltage		V_{GS}	±30	
Continuous Drain Current	T_C=25°C	I_D	30.0	A
	T_C=100°C		18.5	
Pulsed Drain Current	T_C=25°C	I_{DM}	69	A
Single Pulse Avalanche Energy		E_{AS}	670	mJ
MOSFET dv/dt ruggedness		dv/dt	50	V/ns
Power Dissipation	T_C=25°C	P_D	235	W
	T_C=100°C		94	
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55~150	°C

Thermal Characteristics

PARAMETER		SYMBOL	MAXIMUM	UNITS
Thermal Resistance	Junction-to-Case	$R_{\theta JC}$	0.53	°C/W
	Junction-to-Ambient (Note 3)	$R_{\theta JA}$	62.5	°C/W

Electrical Characteristics (T_A = 25 °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250uA	600	710	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	2	3.0	4	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=12A (Note 1)	-	104	120	mΩ
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=600V, V_{GS}=0V	-	-	1	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V	-	-	±100	nA
Transfer characteristics	gfs	V_{DS}=20V, I_D=22A	-	24	-	S
Dynamic (Note 5)						
Total Gate Charge	Q_g	V_{DS}=480V, I_D=22A, V_{GS}=10V	-	51	-	nC
Gate-Source Charge	Q_{gs}		-	11	-	
Gate-Drain Charge	Q_{gd}		-	19	-	
Input Capacitance	Ciss	V_{DS}=400V, V_{GS}=0V, f=250kHz	-	1960	-	pF
Output Capacitance	Coss		-	66	-	
Reverse Transfer Capacitance	Crss		-	7	-	
Effective Output Capacitance Energy Related	$C_{o(er)}$	V_{DS}=0V to 400V, V_{GS}=0V, f=250kHz (Note 4)	-	95	-	
Turn-On Delay Time	$t_{d(on)}$	V_{DD}=300V, I_D=22A, V_{GS}=10V, R_G=25Ω (Note 2)	-	43	-	ns
Turn-On Rise Time	t_r		-	76	-	
Turn-Off Delay Time	$t_{d(off)}$		-	173	-	
Turn-Off Fall Time	t_f		-	81	-	
Gate Resistance	Rg	f=1.0MHz	-	2.3	-	Ω
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S		-	-	30	A
Diode Forward Voltage	V_{SD}	I_S=24A, V_{GS}=0V	-	0.90	1.5	V
Reverse Recovery Charge	Q_{rr}	I_S=22A di/dt=100A/μs	-	6.6	-	μC
Reverse Recovery Time	T_{rr}		-	410	-	ns

NOTES :

1. Pulse width≤300us, Duty cycle≤2%
2. Essentially independent of operating temperature typical characteristics.
3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance.
4. $C_{o(er)}$ is a capacitance that gives the same stored energy as Coss while V_{DS} is rising from 0V to 80% $V_{(BR)DSS}$
5. Guaranteed by design, not subject to production testing

TYPICAL CHARACTERISTIC CURVES

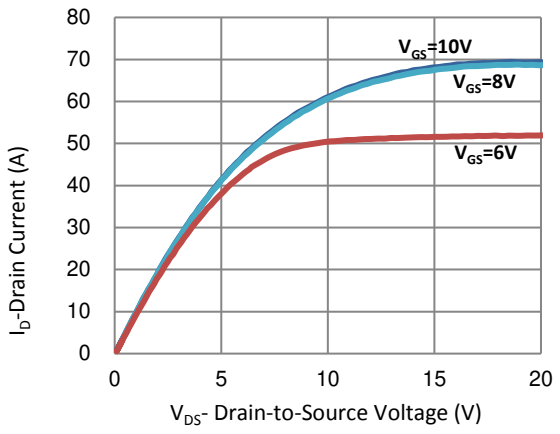


Fig.1 Output Characteristics

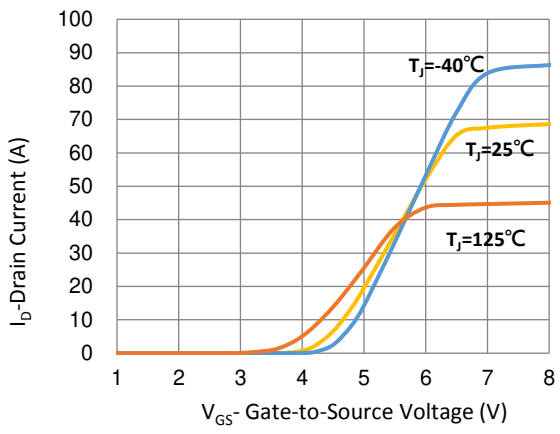


Fig.2 Transfer Characteristics

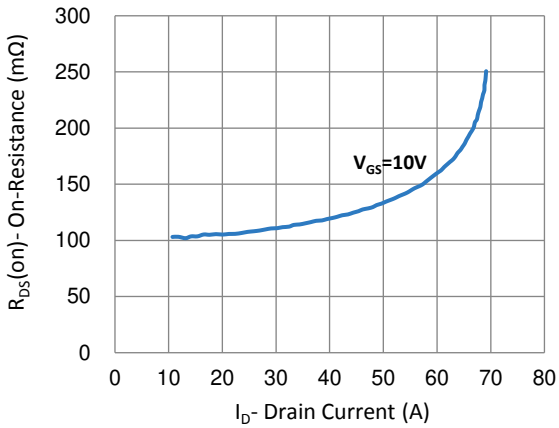


Fig.3 On-Resistance vs. Drain Current

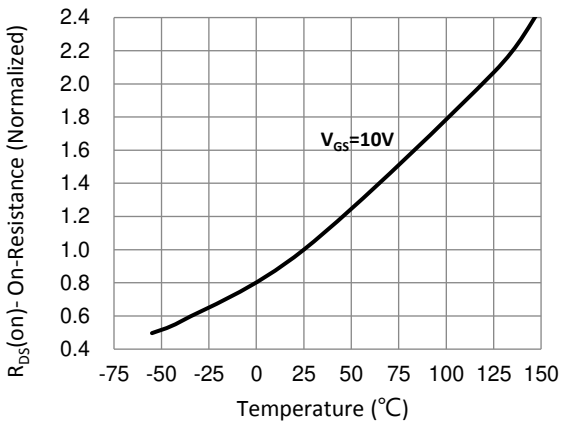


Fig.4 On-Resistance vs. Junction Temperature

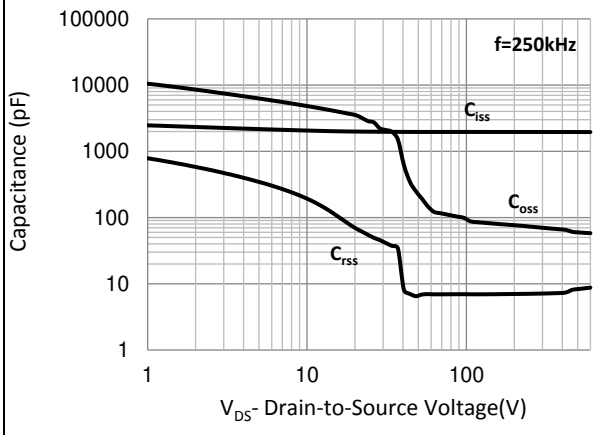


Fig.5 Capacitance vs. Drain-Source Voltage

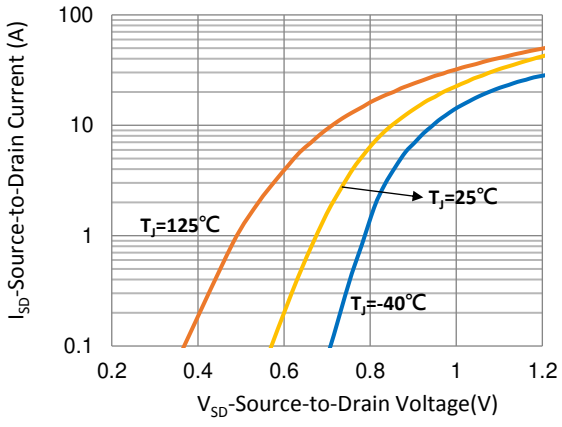


Fig.6 Source-Drain Diode Forward Voltage

TYPICAL CHARACTERISTIC CURVES

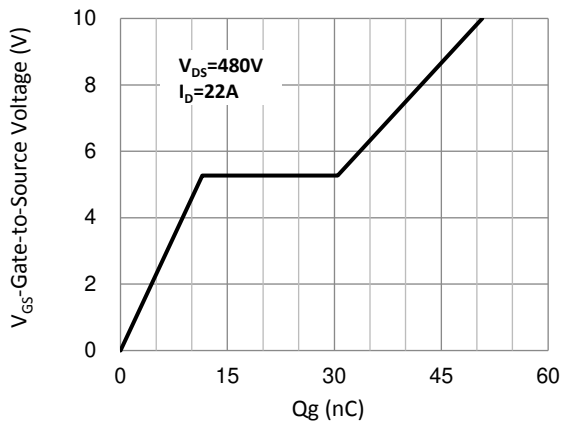


Fig.7 Gate-Charge Characteristics

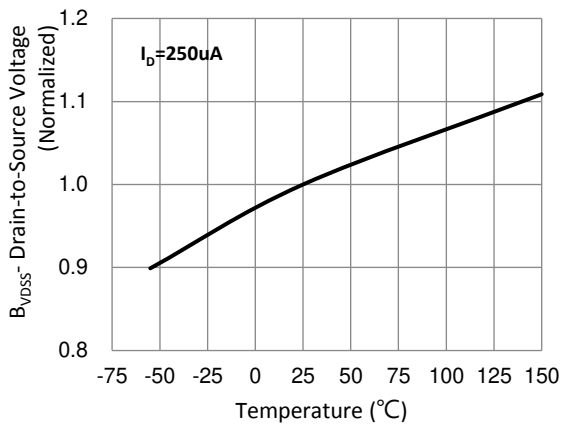


Fig.8 Breakdown Voltage Variation vs. Temperature

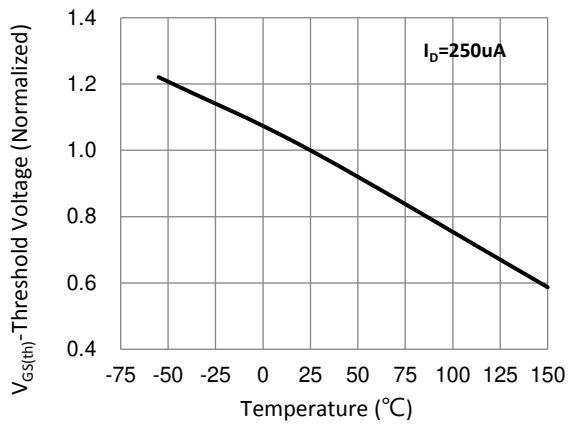


Fig.9 Threshold Voltage Variation with Temperature

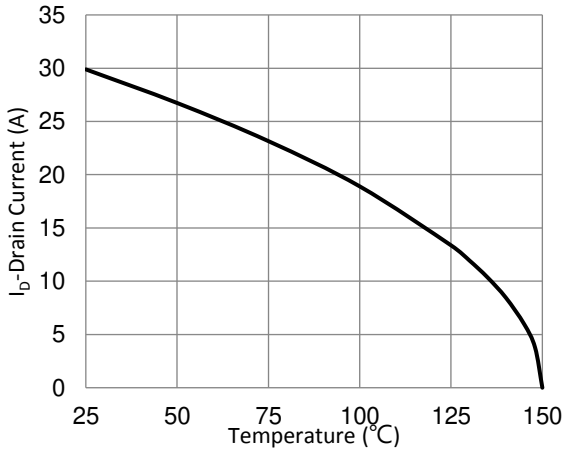


Fig.10 Drain Current vs. Case Temperature

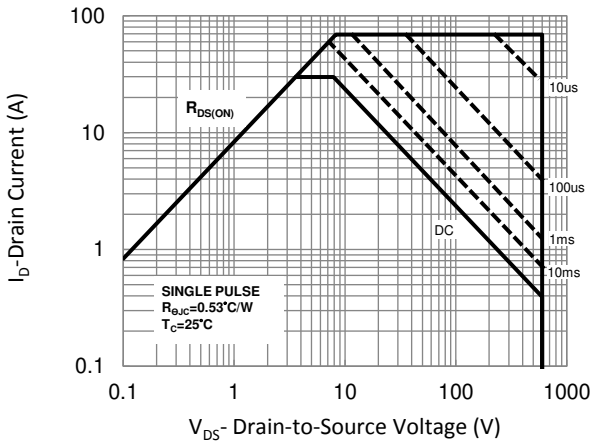


Fig.11 Maximum Safe Operating Area

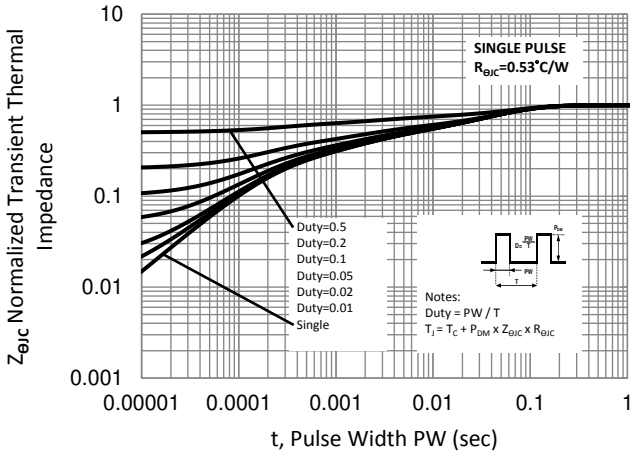


Fig.12 Normalized Transient Thermal Impedance

TYPICAL CHARACTERISTIC CURVES

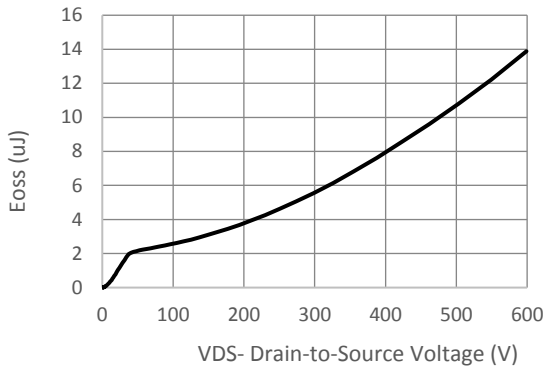


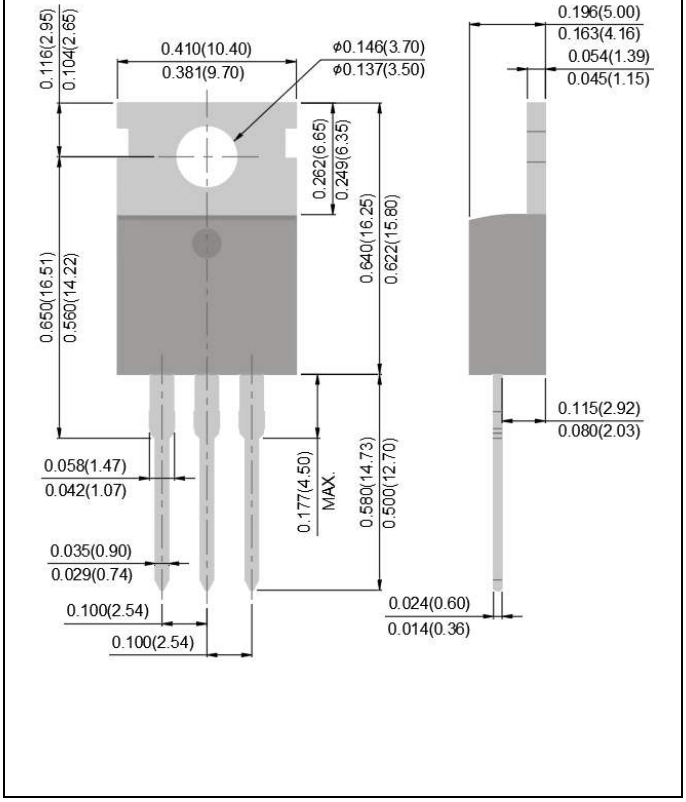
Fig.13 Typ. Coss Stored Energy

Product and Packing Information

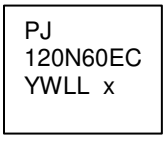
Part No.	Package Type	Packing Type	Marking
PJMP120N60EC	TO-220AB-L	50pcs / Tube	120N60EC

Packaging Information

TO-220AB-L Dimension **Unit: inch(mm)**



Marking Diagram



Y = Year Code
W = Week Code (A~Z)
LL = Lot Code (00~99)
x = Production Line Code

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